2SC5200

Rev.E Nov.-2016

蓝箭电子 BLUE ROCKET ELECTRONICS

DATA SHEET

/ Descriptions

TO-3P NPN Silicon NPN transistor in a TO-3P Plastic Package.

/ Features

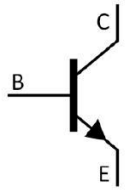
100W 2SA1943

Recommend for 100W high fidelity audio frequency amplifier output stage, Complementary to 2SA1943.

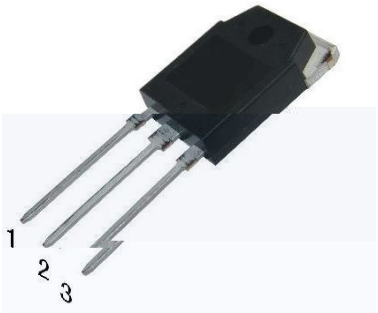
/ Applications

Power amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

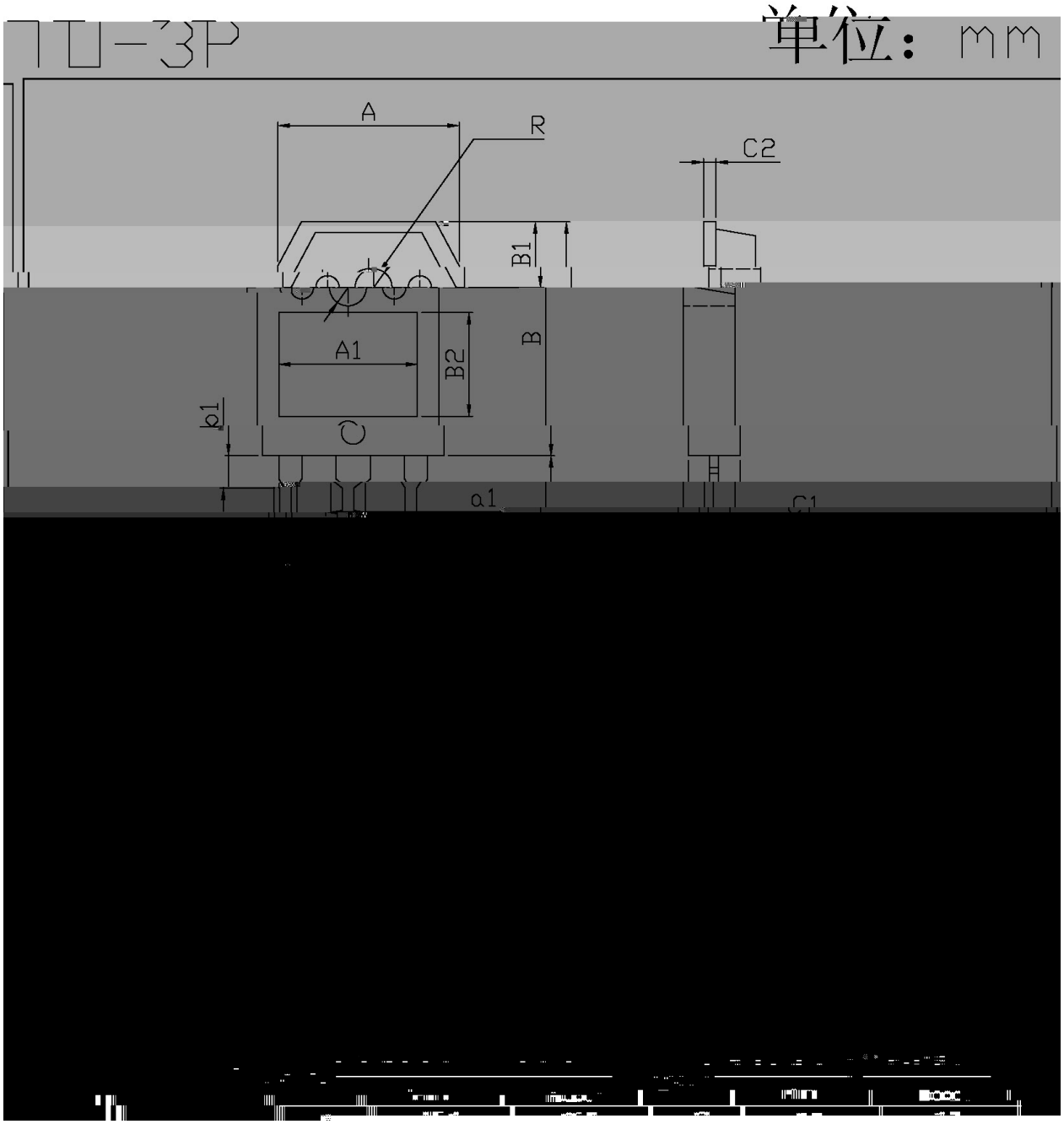
/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	R	O
h_{FE} Range	55~110	80~160

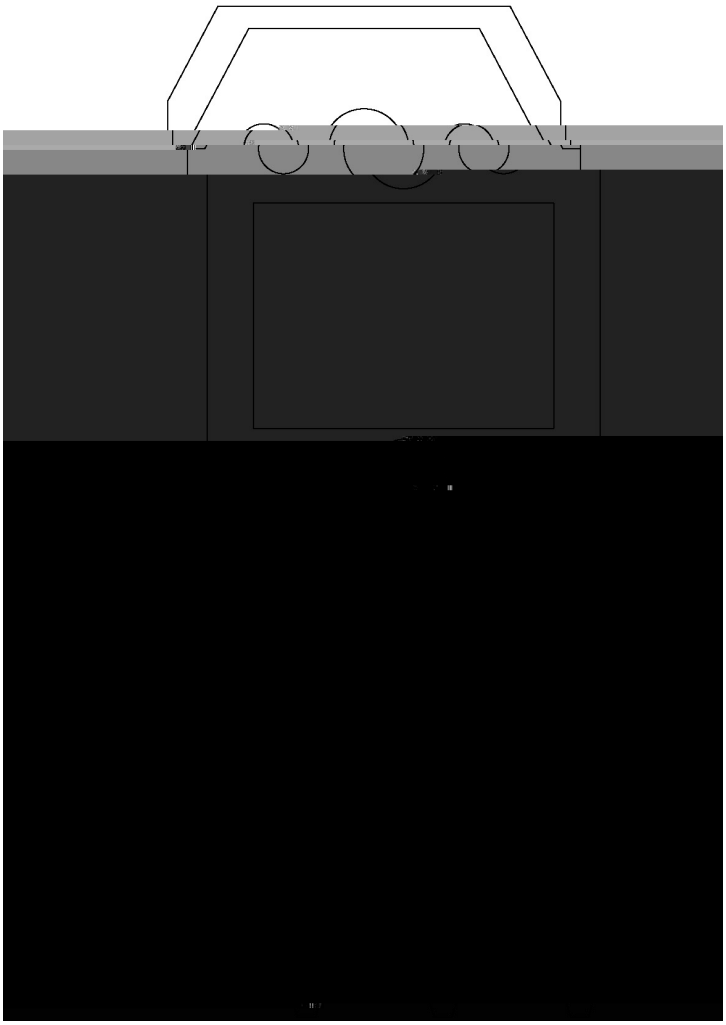
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	230	V
Collector to Emitter Voltage	V_{CEO}	230	V
Emitter to Base Voltage	V_{EBO}	5	V
Collector Current - Continuous	I_C	15	A
Peak Collector Current	I_{CP}	30	A
Base Current	I_B	1.5	A
Collector Power Dissipation	$P_{C(TC=25\ )}$	150	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CEO}	I_C=50mA I_B=0	230			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=230V I_E=0			5	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=5.0V I_C=0			5	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=5.0V I_C=1.0A	55		160	
	$h_{FE(2)}$	V_{CE}=5.0V I_C=7.0A	35	60		
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=8.0A I_B=0.8A		0.4	3	V
Base to Emitter Voltage	V_{BE}	V_{CE}=5.0V I_C=7.0A		1	1.5	V
Transition Frequency	f_T	V_{CE}=5.0V I_C=1.0A		30		MHz

/ Package Dimensions



/ Marking Instructions



BR

C5200

O: h_{FE}

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Note:

BR: Company Code.

C5200: Product Typm